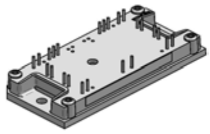
flowPACK 1 H | **650V/75A**

Features

- Low inductive 12mm flow1 package
- H-Bridge topology
- High-speed IGBT + ultrafast FWD
- Temperature sensor

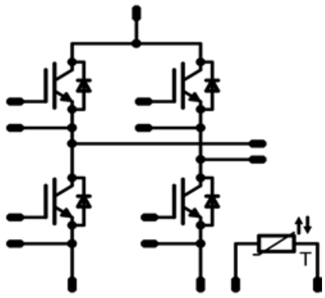
flowPACK 1 H



Target Applications

- Solar inverter
- Power Supply
- Inverter based welding

Schematic



Types

- 10-FY064PA075SG-M583F08

Maximum Ratings

T_j=25°C, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
H-Bridge IGBT					
Collector-emitter break down voltage	V_{CE}			650	V
DC collector current	I_{DC}	$T_j=T_j$max	T_h=80°C T_c=80°C	53 71	A
Pulsed collector current	I_{Cpulse}	t_p limited by $T_j$max		225	A
Turn off safe operating area		VCE ≤ 650V, Tj ≤ Top max		150	A
Power dissipation per IGBT	P_{tot}	$T_j=T_j$max	T_h=80°C T_c=80°C	93 141	W
Gate-emitter peak voltage	V_{GE}			±20	V
Short circuit ratings	t_{SC} V_{CC}	T_j≤150°C V_{GE}=15V		5 400	µs V
Maximum Junction Temperature	$T_j$max			175	°C
H-Bridge FWD					
Peak Repetitive Reverse Voltage	V_{RRM}	T_j=25°C		650	V
DC forward current	I_F	$T_j=T_j$max	T_h=80°C T_c=80°C	42 55	A
Repetitive peak forward current	I_{FRM}	t_p limited by $T_j$max		225	A
Power dissipation per Diode	P_{tot}	$T_j=T_j$max	T_h=80°C T_c=80°C	70 106	W
Maximum Junction Temperature	$T_j$max			175	°C

Maximum Ratings

T_j=25°C, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{op}			-40…+(Tjmax - 25)	°C
Insulation Properties					
Insulation voltage	V_{is}	t=2s	DC voltage	4000	V
Creepage distance				min 12,7	mm
Clearance				min 12,7	mm
Comparative tracking index	CTI			>200	

Characteristic Values

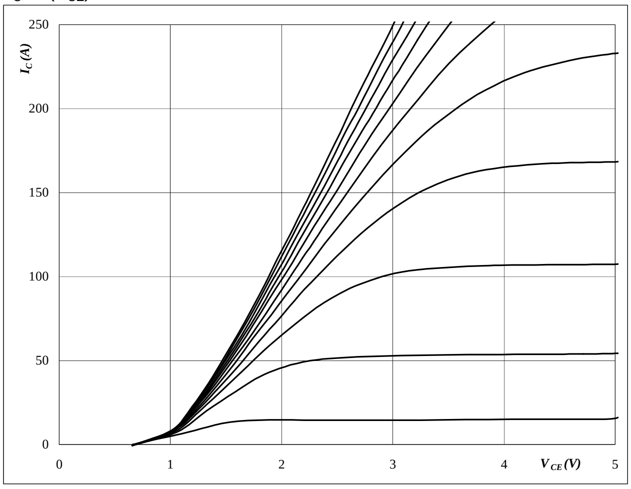
Parameter	Symbol	Conditions	V_{GE} [V] or V_{GS} [V]	V_r [V] or V_{CE} [V] or V_{DS} [V]	I_C [A] or I_F [A] or I_D [A]	T_j	Min	Typ	Max	Unit
H-Bridge IGBT										
Gate emitter threshold voltage	$V_{GE(th)}$	$V_{CE}=V_{GE}$			0,0012	Tj=25°C Tj=150°C	4,2	5,1	5,6	V
Collector-emitter saturation voltage	$V_{CE(sat)}$		15		75	Tj=25°C Tj=150°C	1,38	1,72 1,97	2,5	V
Collector-emitter cut-off current incl. Diode	I_{CES}		0	650		Tj=25°C Tj=150°C			15	uA
Gate-emitter leakage current	I_{GES}		20	0		Tj=25°C Tj=150°C			150	nA
Integrated Gate resistor	R_{gint}							none		Ω
Turn-on delay time	$t_{d(on)}$	Rgoff=4 Ω Rgon=4 Ω	±15	300	75	Tj=25°C Tj=150°C		85 87		ns
Rise time	t_r					Tj=25°C Tj=150°C		14 17		
Turn-off delay time	$t_{d(off)}$					Tj=25°C Tj=150°C		125 147		
Fall time	t_f					Tj=25°C Tj=150°C		18 31		
Turn-on energy loss per pulse	E_{on}					Tj=25°C Tj=150°C		0,51 0,9		mWs
Turn-off energy loss per pulse	E_{off}					Tj=25°C Tj=150°C		0,66 1,17		
Input capacitance	C_{ies}	f=1MHz	0	25		Tj=25°C		4620		pF
Reverse transfer capacitance	C_{rss}							137		
Gate charge	Q_{Gate}		15	480	75	Tj=25°C		470		nC
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						1,02		K/W
H-Bridge FWD										
Diode forward voltage	V_F				50	Tj=25°C Tj=125°C		2,4 1,9	3	V
Peak reverse recovery current	I_{RRM}	Rgon=4 Ω	±15	300	75	Tj=25°C Tj=150°C		63 82		A
Reverse recovery time	t_{rr}					Tj=25°C Tj=150°C		17 94		ns
Reverse recovered charge	Q_{rr}					Tj=25°C Tj=150°C		0,96 2,94		µC
Peak rate of fall of recovery current	di(rec)max/dt					Tj=25°C Tj=150°C		15698 5163		A/µs
Reverse recovered energy	Erec					Tj=25°C Tj=150°C		0,13 0,54		mWs
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						1,36		K/W
Thermistor										
Rated resistance	R					T=25°C		22000		Ω
Deviation of R25	ΔR/R	R100=1486 Ω				T=100°C	-5		5	%
Power dissipation	P					T=25°C		200		mW
Power dissipation constant						Tj=25°C		2		mW/K
B-value	$B_{(25/50)}$	Tol. ±3%				Tj=25°C		3950		K
B-value	$B_{(25/100)}$	Tol. ±3%				Tj=25°C		3996		K
Vincotech NTC Reference									B	

Output Inverter

Figure 1 Output inverter IGBT

Typical output characteristics

$I_C = f(V_{CE})$



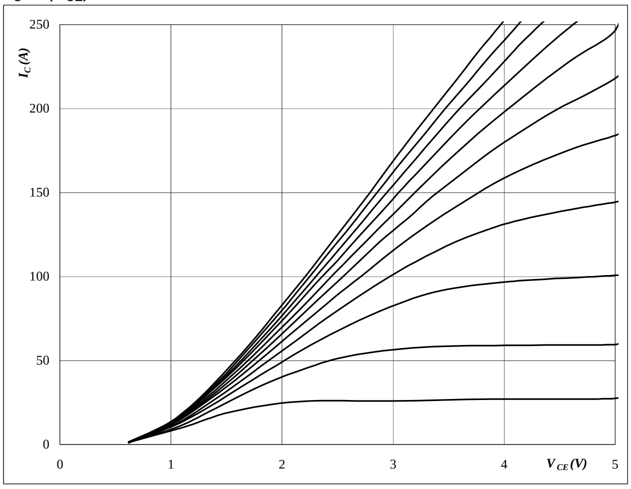
At

t_p =	250	µs
T_j =	25	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

Figure 2 Output inverter IGBT

Typical output characteristics

$I_C = f(V_{CE})$



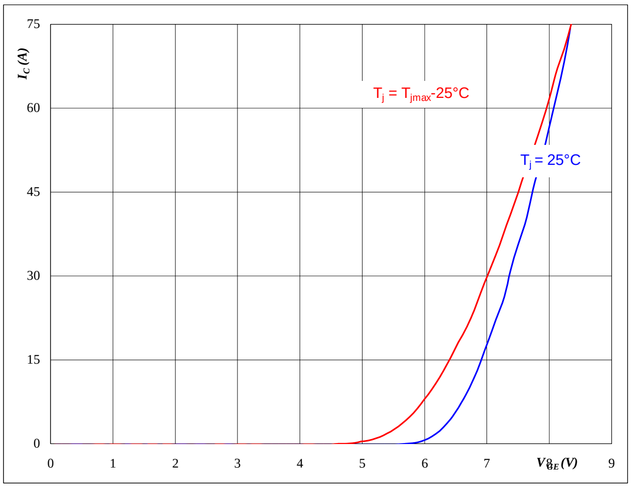
At

t_p =	250	µs
T_j =	150	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

Figure 3 Output inverter IGBT

Typical transfer characteristics

$I_C = f(V_{GE})$



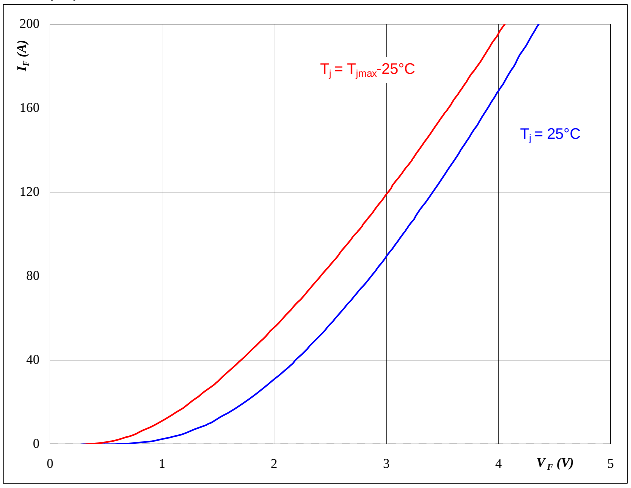
At

t_p =	250	µs
V_{CE} =	10	V

Figure 4 Output inverter FWD

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



At

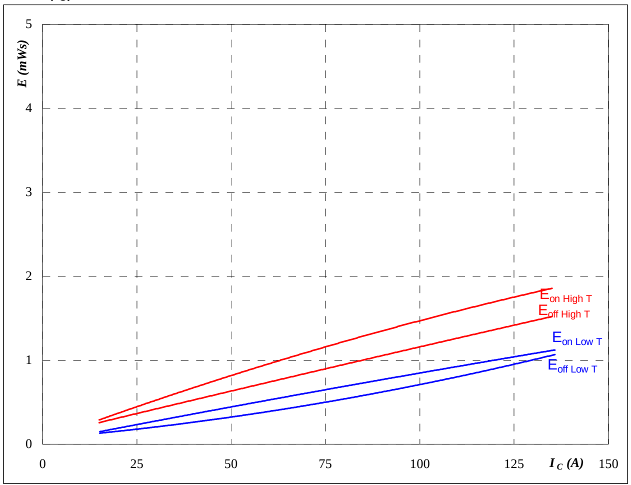
t_p =	250	µs

Output Inverter

Figure 5 Output inverter IGBT

Typical switching energy losses
as a function of collector current

$E = f(I_C)$



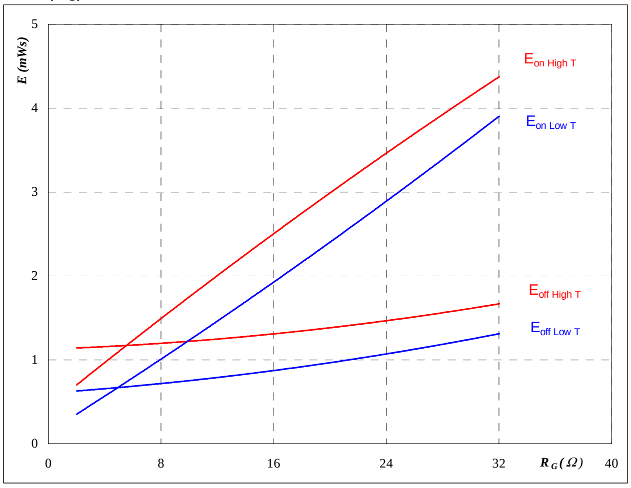
With an inductive load at

T_j =	25/150	°C
V_{CE} =	300	V
V_{GE} =	±15	V
R_{gon} =	4	Ω
R_{goff} =	4	Ω

Figure 6 Output inverter IGBT

Typical switching energy losses
as a function of gate resistor

$E = f(R_G)$



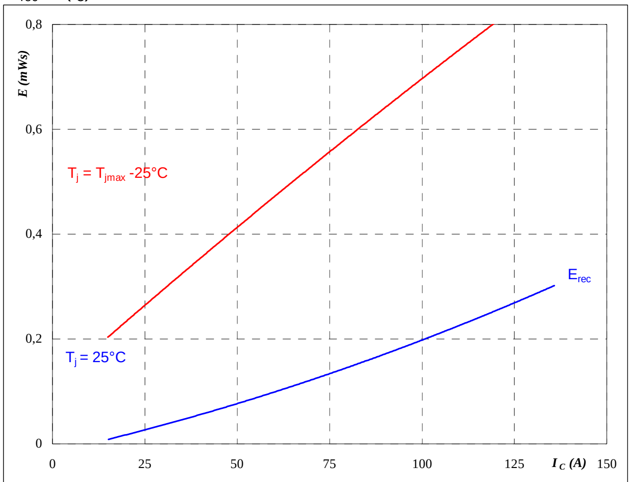
With an inductive load at

T_j =	25/150	°C
V_{CE} =	300	V
V_{GE} =	±15	V
I_C =	75	A

Figure 7 Output inverter FWD

Typical reverse recovery energy loss
as a function of collector current

$E_{rec} = f(I_C)$



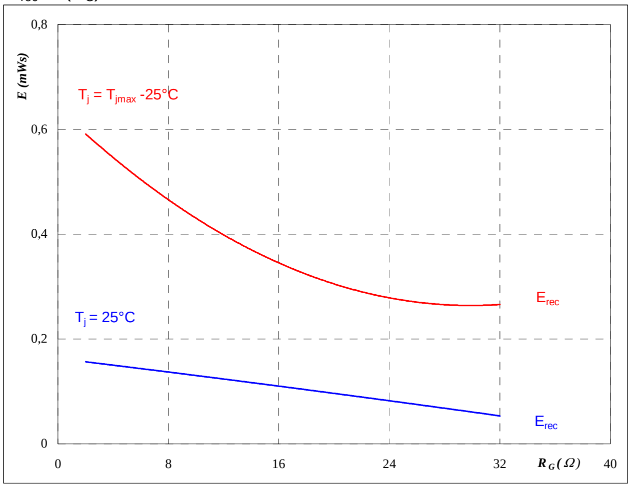
With an inductive load at

T_j =	25/150	°C
V_{CE} =	300	V
V_{GE} =	±15	V
R_{gon} =	4	Ω

Figure 8 Output inverter FWD

Typical reverse recovery energy loss
as a function of gate resistor

$E_{rec} = f(R_G)$



With an inductive load at

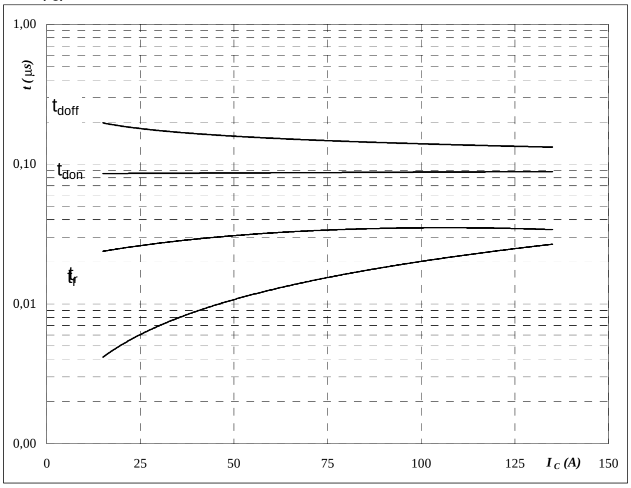
T_j =	25/150	°C
V_{CE} =	300	V
V_{GE} =	±15	V
I_C =	75	A

Output Inverter

Figure 9 Output inverter IGBT

Typical switching times as a function of collector current

t = f(I_C)



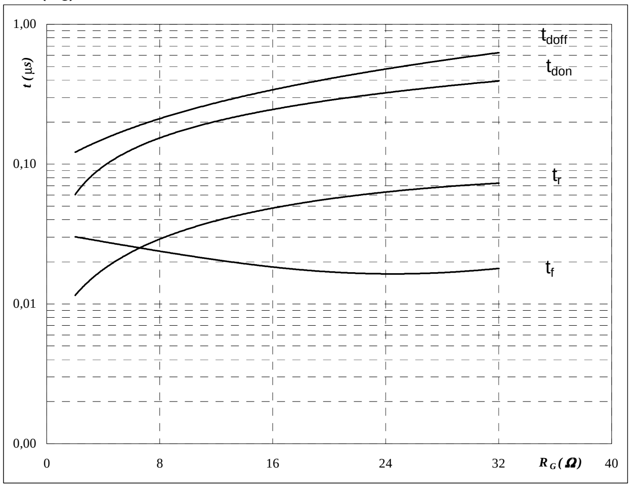
With an inductive load at

T_j =	150	°C
V_{CE} =	300	V
V_{GE} =	±15	V
R_{gon} =	4	Ω
R_{goff} =	4	Ω

Figure 10 Output inverter IGBT

Typical switching times as a function of gate resistor

t = f(R_G)



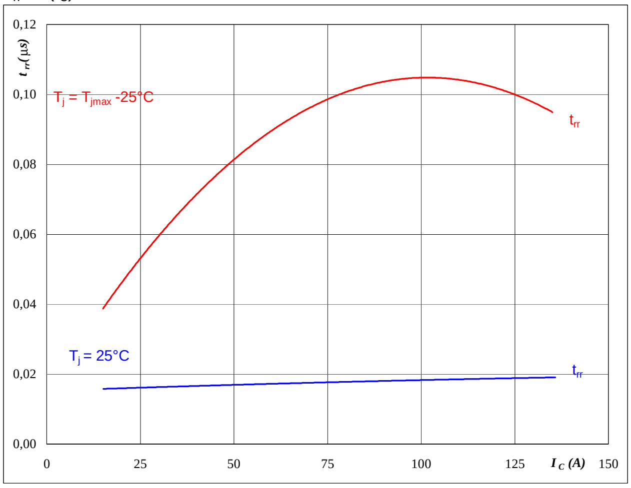
With an inductive load at

T_j =	150	°C
V_{CE} =	300	V
V_{GE} =	±15	V
I_C =	75	A

Figure 11 Output inverter FWD

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



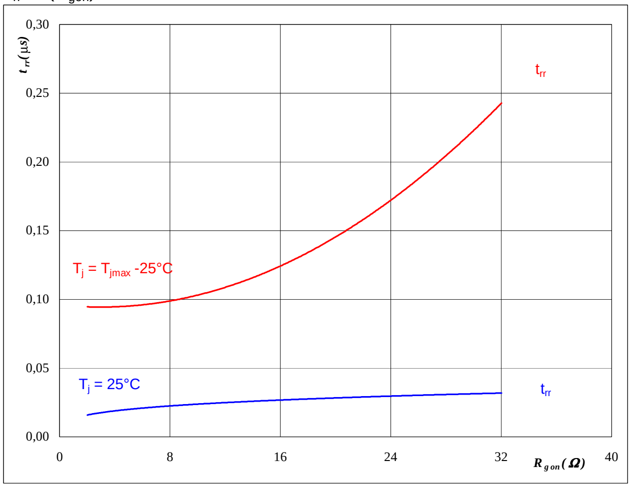
At

T_j =	25/150	°C
V_{CE} =	300	V
V_{GE} =	±15	V
R_{gon} =	4	Ω

Figure 12 Output inverter FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



At

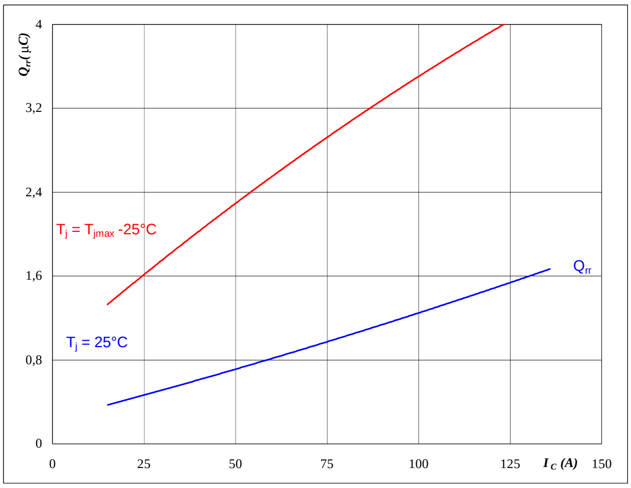
T_j =	25/150	°C
V_R =	300	V
I_F =	75	A
V_{GE} =	±15	V

Output Inverter

Figure 13 Output inverter FWD

Typical reverse recovery charge as a function of collector current

$Q_{rr} = f(I_C)$



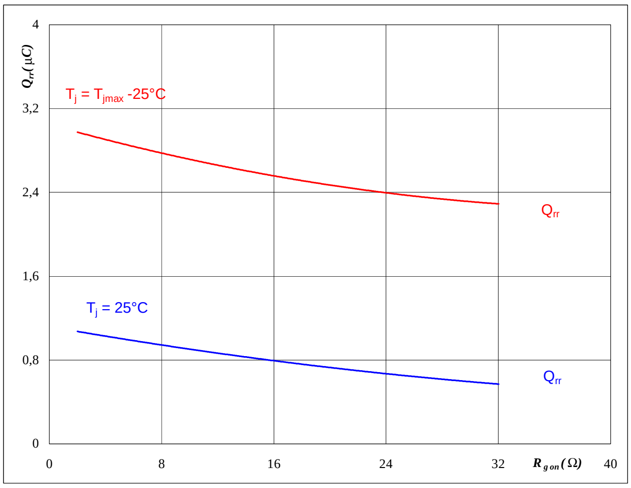
At

T_j =	25/150	°C
V_{CE} =	300	V
V_{GE} =	±15	V
R_{gon} =	4	Ω

Figure 14 Output inverter FWD

Typical reverse recovery charge as a function of IGBT turn on gate resistor

$Q_{rr} = f(R_{gon})$



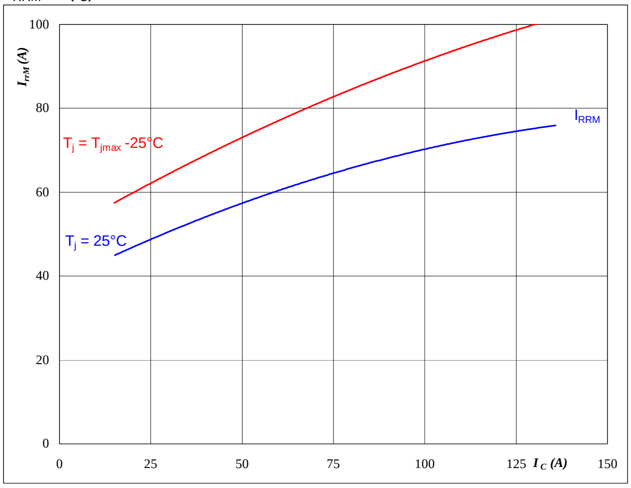
At

T_j =	25/150	°C
V_R =	300	V
I_F =	75	A
V_{GE} =	±15	V

Figure 15 Output inverter FWD

Typical reverse recovery current as a function of collector current

$I_{RRM} = f(I_C)$



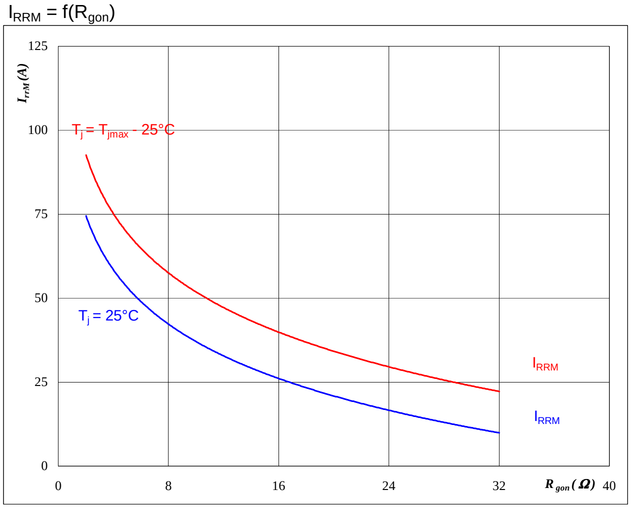
At

T_j =	25/150	°C
V_{CE} =	300	V
V_{GE} =	±15	V
R_{gon} =	4	Ω

Figure 16 Output inverter FWD

Typical reverse recovery current as a function of IGBT turn on gate resistor

$I_{RRM} = f(R_{gon})$



At

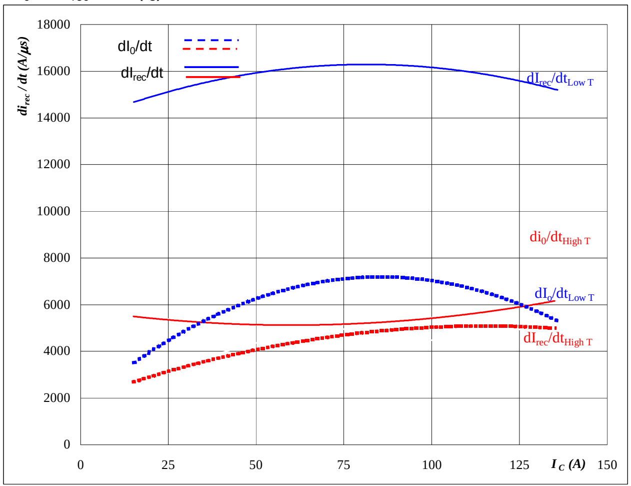
T_j =	25/150	°C
V_R =	300	V
I_F =	75	A
V_{GE} =	±15	V

Output Inverter

Figure 17 — Output inverter FWD

Typical rate of fall of forward and reverse recovery current as a function of collector current

$dI_0/dt, dI_{rec}/dt = f(I_C)$



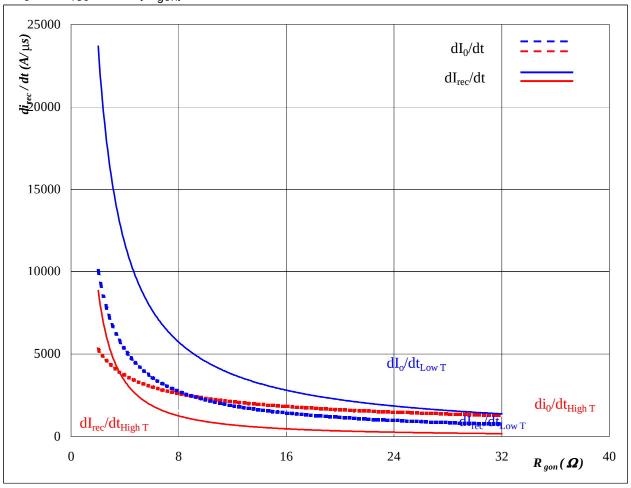
At

T_j =	25/150	°C
V_{CE} =	300	V
V_{GE} =	±15	V
R_{gon} =	4	Ω

Figure 18 — Output inverter FWD

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

$dI_0/dt, dI_{rec}/dt = f(R_{gon})$



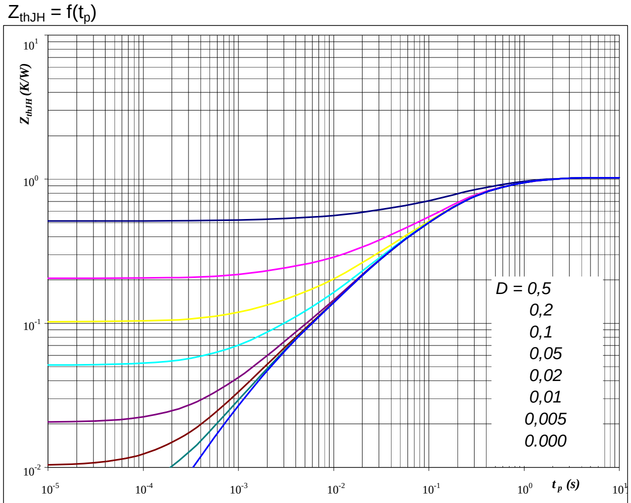
At

T_j =	25/150	°C
V_R =	300	V
I_F =	75	A
V_{GE} =	±15	V

Figure 19 — Output inverter IGBT

IGBT transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

D =	t_p / T		
R_{thJH} =	1,02	K/W	0,87

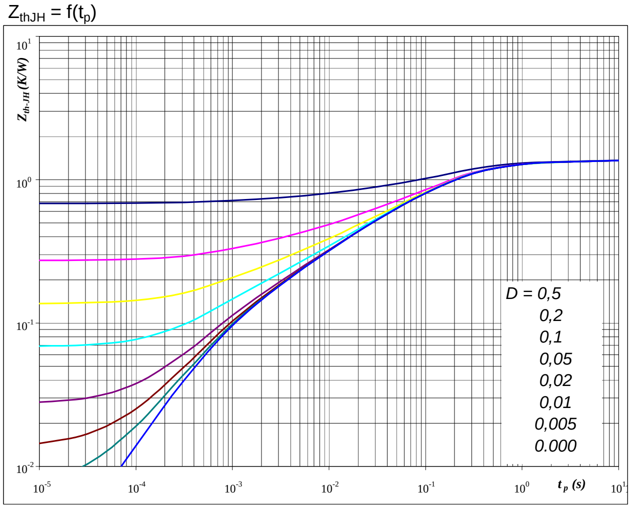
IGBT thermal model values

Thermal grease R (C/W)	Tau (s)	Phase change interface R (C/W)	Tau (s)
0,20	9,7E-01	0,17	8,2E-01
0,49	2,1E-01	0,42	1,8E-01
0,19	6,2E-02	0,16	5,2E-02
0,11	1,4E-02	0,09	1,2E-02
0,03	1,7E-03	0,03	1,4E-03

Figure 20 — Output inverter FWD

FWD transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

D =	t_p / T		
R_{thJH} =	1,36	K/W	1,16

FWD thermal model values

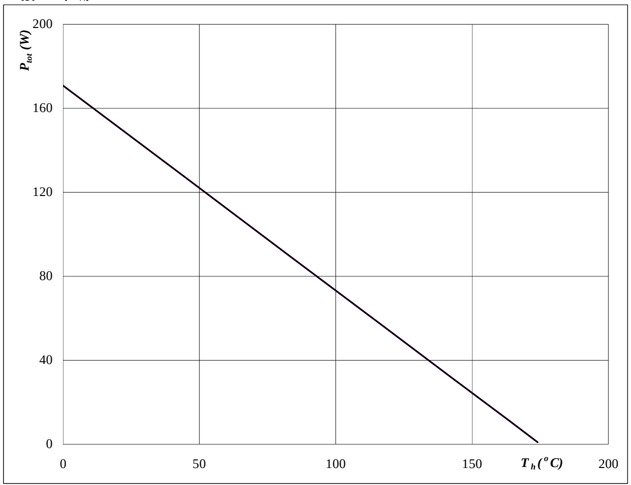
Thermal grease R (C/W)	Tau (s)	Phase change interface R (C/W)	Tau (s)
0,09	3,0E+00	0,07	2,5E+00
0,40	3,3E-01	0,34	2,8E-01
0,49	9,8E-02	0,41	8,3E-02
0,22	1,7E-02	0,19	1,5E-02
0,10	3,2E-03	0,09	2,8E-03
0,06	6,7E-04	0,05	5,7E-04

Output Inverter

Figure 21 Output inverter IGBT

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$

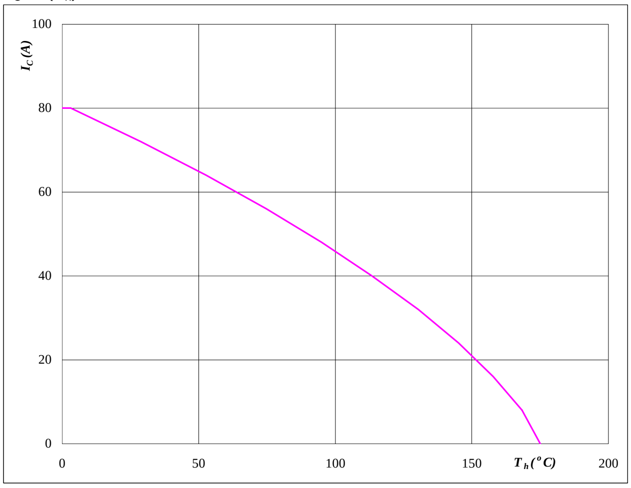


At
T_j = 175 °C

Figure 22 Output inverter IGBT

Collector current as a function of heatsink temperature

$I_C = f(T_h)$

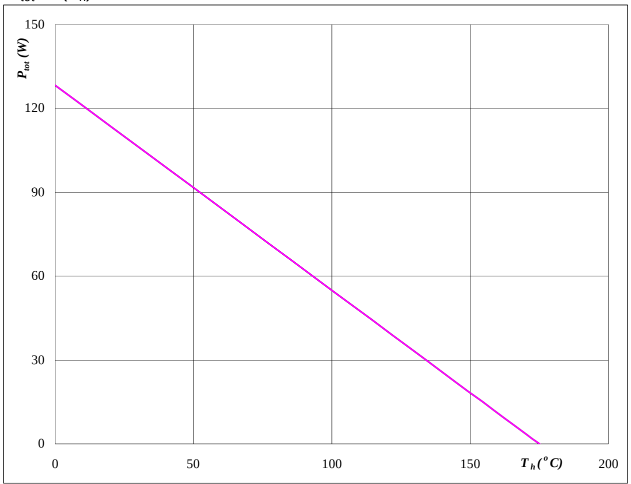


At
T_j = 175 °C
V_{GE} = 15 V

Figure 23 Output inverter FWD

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$

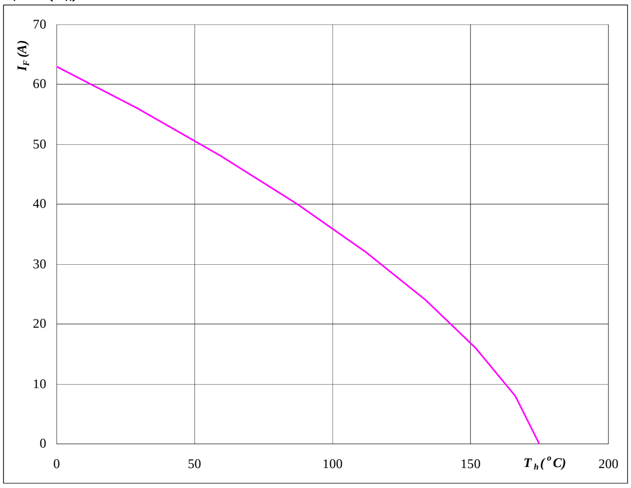


At
T_j = 175 °C

Figure 24 Output inverter FWD

Forward current as a function of heatsink temperature

$I_F = f(T_h)$



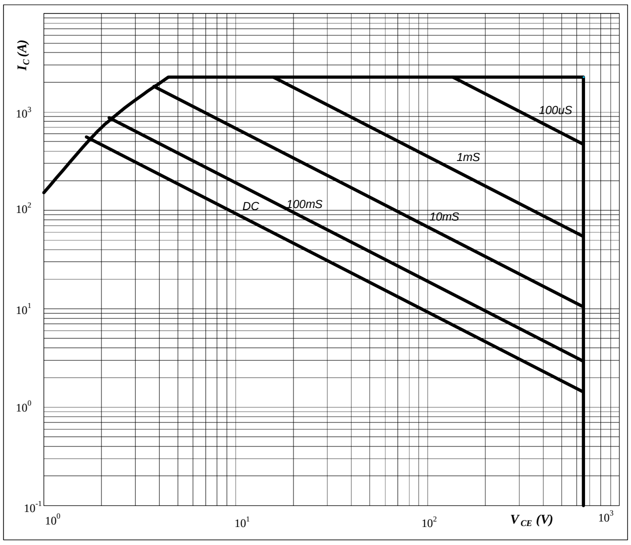
At
T_j = 175 °C

Output Inverter

Figure 25 Output inverter IGBT

Safe operating area as a function of collector-emitter voltage

$I_C = f(V_{CE})$



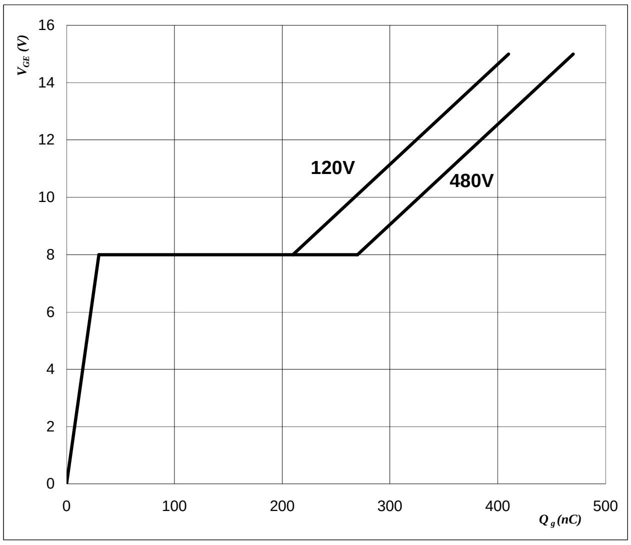
At

D =	single pulse	
T_h =	80	ºC
V_{GE} =	±15	V
T_j =	T_{jmax}	ºC

Figure 26 Output inverter IGBT

Gate voltage vs Gate charge

$V_{GE} = f(Q_{GE})$



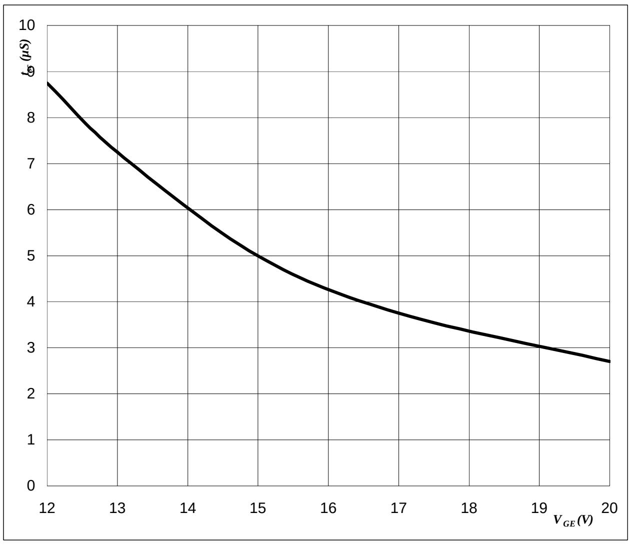
At

I_C =	75	A

Figure 27 Output inverter IGBT

Short circuit withstand time as a function of gate-emitter voltage

$t_{sc} = f(V_{GE})$



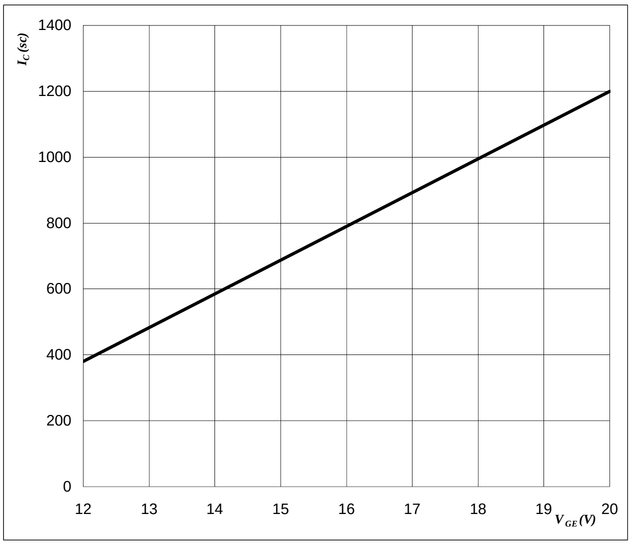
At

V_{CE} =	400	V
T_j ≤	150	ºC

Figure 28 Output inverter IGBT

Typical short circuit collector current as a function of gate-emitter voltage

$V_{GE} = f(Q_{GE})$



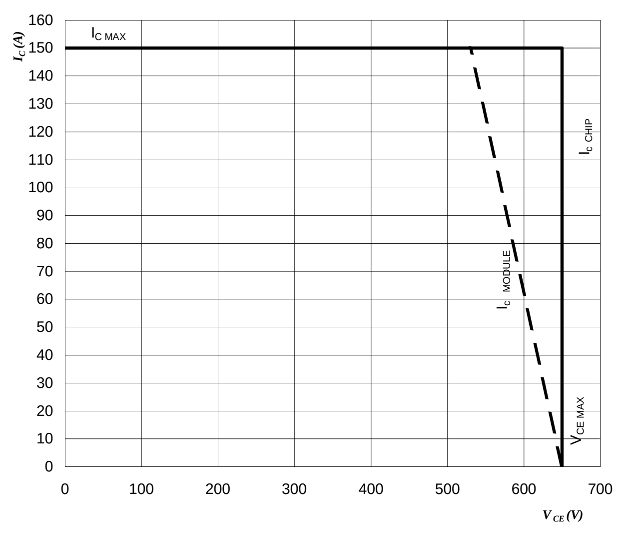
At

V_{CE} ≤	400	V
T_j =	150	ºC

Figure 29 IGBT

Reverse bias safe operating area

$I_C = f(V_{CE})$



At

T_j = T_{jmax}-25 ºC

Switching mode : 3phase SPWM

Thermistor

Figure 1 Thermistor

Typical NTC characteristic
as a function of temperature

$R_T = f(T)$

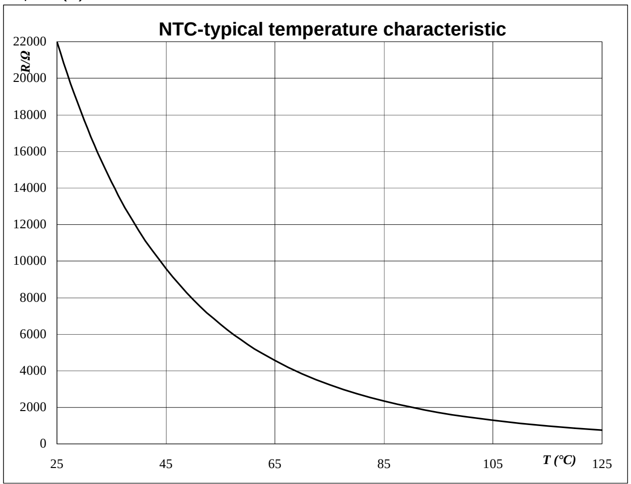


Figure 2 Thermistor

Typical NTC resistance values

$$R(T) = R_{25} \cdot e^{\left(B_{25/100}\left(\frac{1}{T} - \frac{1}{T_{25}}\right)\right)} \quad [\Omega]$$

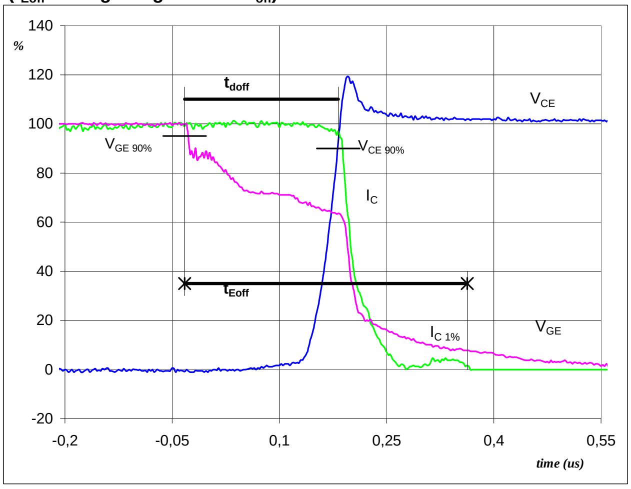
Switching Definitions Output Inverter

General conditions

T_j	=	150 °C
R_{gon}	=	8 Ω
R_{goff}	=	8 Ω

Figure 1 Output inverter IGBT

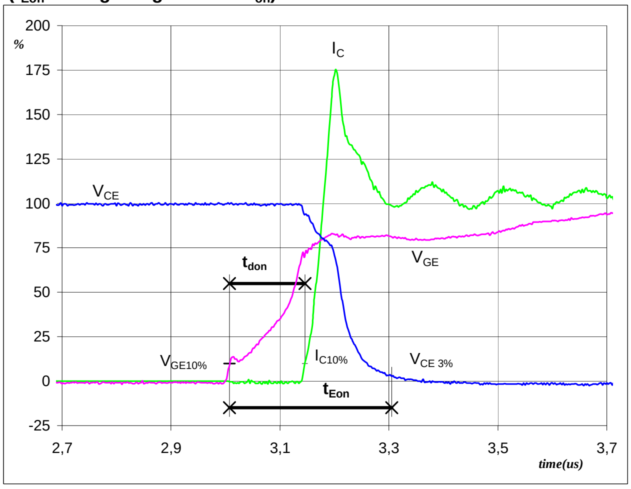
Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff}
(t_{Eoff} = integrating time for E_{off})



V_{GE} (0%) =	-15	V
V_{GE} (100%) =	15	V
V_C (100%) =	300	V
I_C (100%) =	75	A
t_{doff} =	0,21	µs
t_{Eoff} =	0,40	µs

Figure 2 Output inverter IGBT

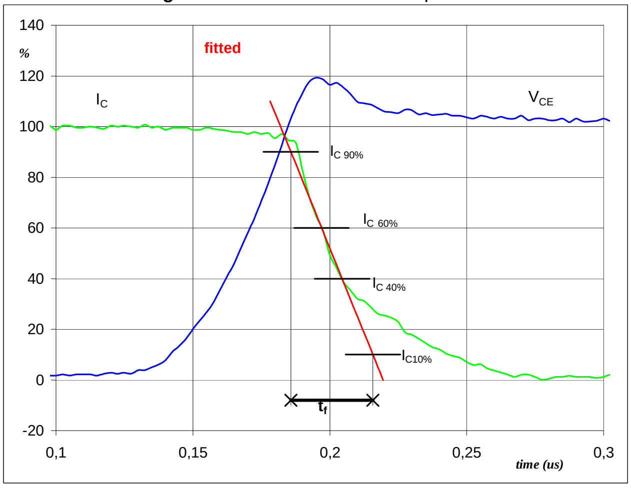
Turn-on Switching Waveforms & definition of tdon, t_{Eon}
(t_{Eon} = integrating time for E_{on})



V_{GE} (0%) =	-15	V
V_{GE} (100%) =	15	V
V_C (100%) =	300	V
I_C (100%) =	75	A
t_{don} =	0,14	µs
t_{Eon} =	0,30	µs

Figure 3 Output inverter IGBT

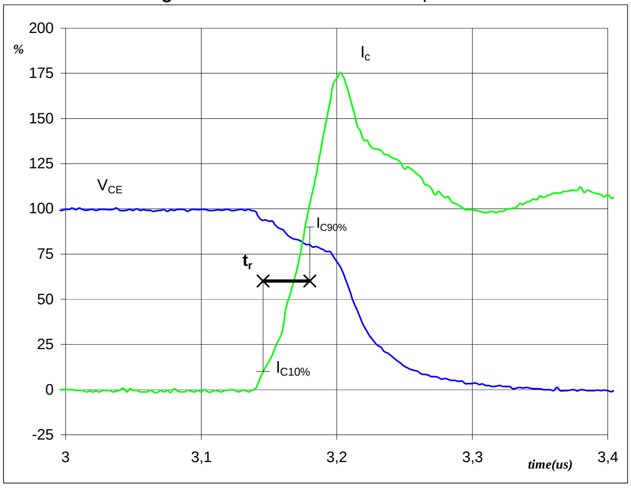
Turn-off Switching Waveforms & definition of t_f



V_C (100%) =	300	V
I_C (100%) =	75	A
t_f =	0,03	µs

Figure 4 Output inverter IGBT

Turn-on Switching Waveforms & definition of t_r

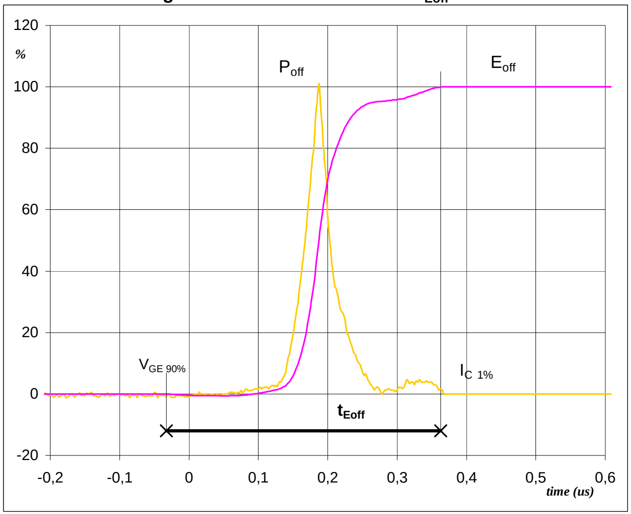


V_C (100%) =	300	V
I_C (100%) =	75	A
t_r =	0,03	µs

Switching Definitions Output Inverter

Figure 5 Output inverter IGBT

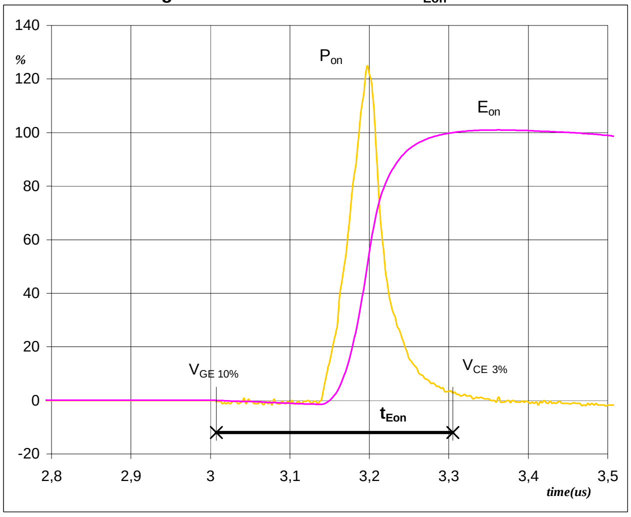
Turn-off Switching Waveforms & definition of t_{Eoff}



P_{off} (100%) =	22,61	kW
E_{off} (100%) =	1,15	mJ
t_{Eoff} =	0,40	μs

Figure 6 Output inverter IGBT

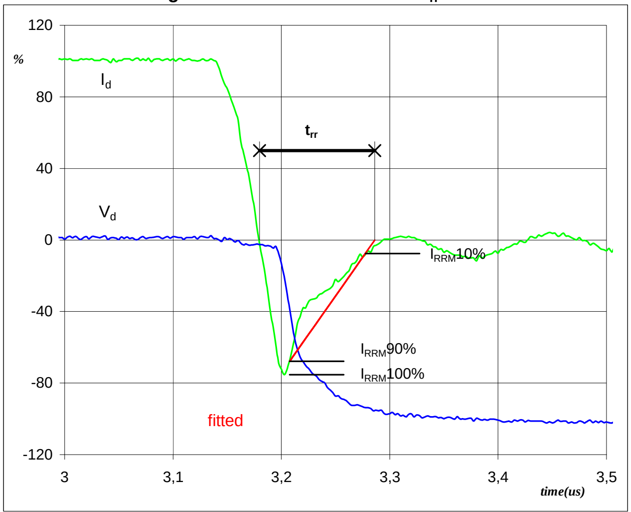
Turn-on Switching Waveforms & definition of t_{Eon}



P_{on} (100%) =	22,61	kW
E_{on} (100%) =	1,52	mJ
t_{Eon} =	0,30	μs

Figure 7 Output inverter IGBT

Turn-off Switching Waveforms & definition of t_{rr}

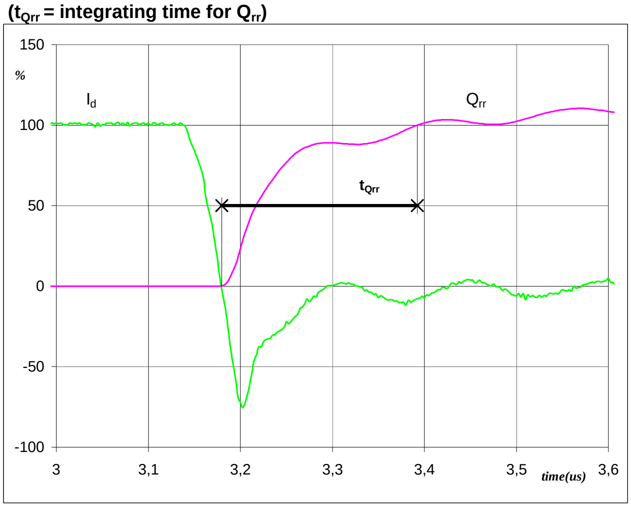


V_d (100%) =	300	V
I_d (100%) =	75	A
I_{RRM} (100%) =	-57	A
t_{rr} =	0,11	μs

Switching Definitions Output Inverter

Figure 8 Output inverter FWD

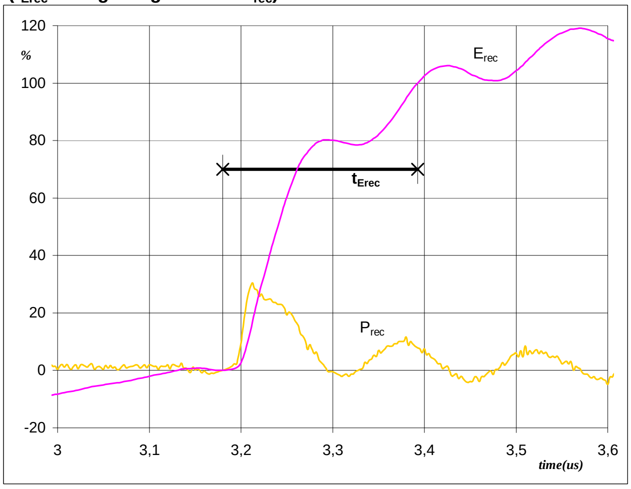
Turn-on Switching Waveforms & definition of t_{Qrr}
(t_{Qrr} = integrating time for Q_{rr})



I_d (100%) =	75	A
Q_{rr} (100%) =	2,94	μC
t_{Qrr} =	0,21	μs

Figure 9 Output inverter FWD

Turn-on Switching Waveforms & definition of t_{Erec}
(t_{Erec}= integrating time for E_{rec})



P_{rec} (100%) =	22,61	kW
E_{rec} (100%) =	0,50	mJ
t_{Erec} =	0,21	μs

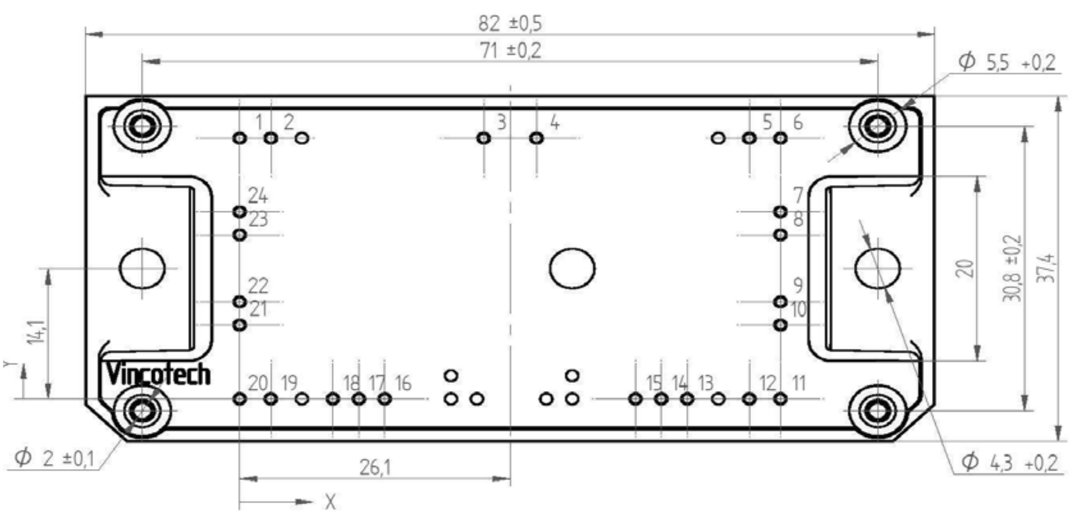
Ordering Code and Marking - Outline - Pinout

Ordering Code & Marking

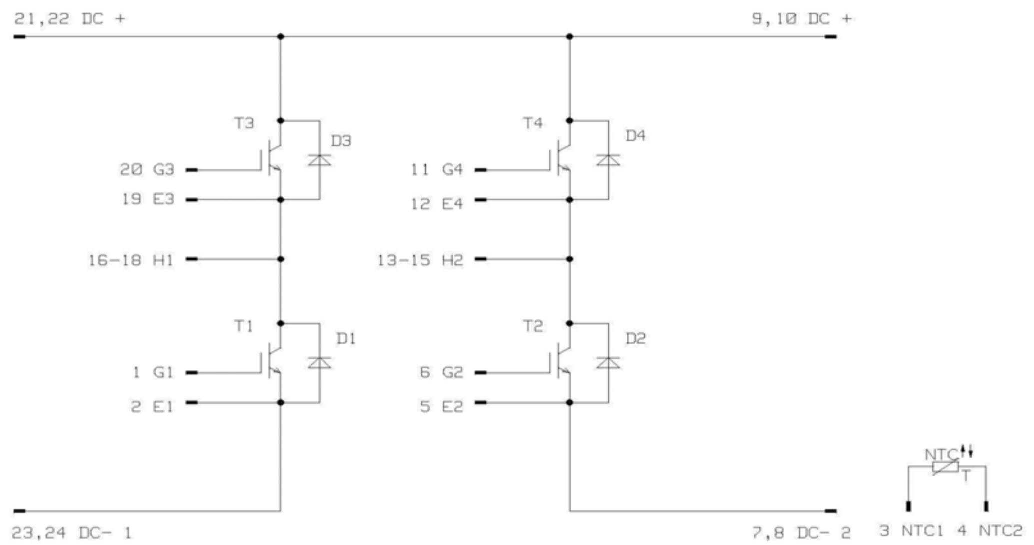
Version	Ordering Code	in DataMatrix as	in packaging barcode as
without thermal paste 12mm housing	10-FY064PA075SG-M583F08	M583F08	M583F08

Outline

Pin table		
Pin	X	Y
1	0	28,2
2	3	28,2
3	23,55	28,2
4	28,65	28,2
5	49,2	28,2
6	52,2	28,2
7	52,2	20,25
8	52,2	17,75
9	52,2	10,5
10	52,2	8
11	52,2	0
12	49,2	0
13	43,2	0
14	40,7	0
15	38,2	0
16	14	0
17	11,5	0
18	9	0
19	3	0
20	0	0
21	0	8
22	0	10,5
23	0	17,75
24	0	20,25



Pinout



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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.